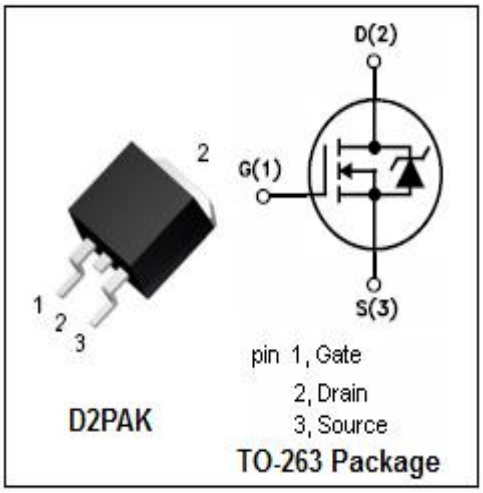
Isc N-Channel MOSFET Transistor IPB200N25N3G



- **FEATURES**
- With TO-263(D^2 PAK) packaging
- High speed switching
- Low gate input resistance
- Standard level gate drive
- Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

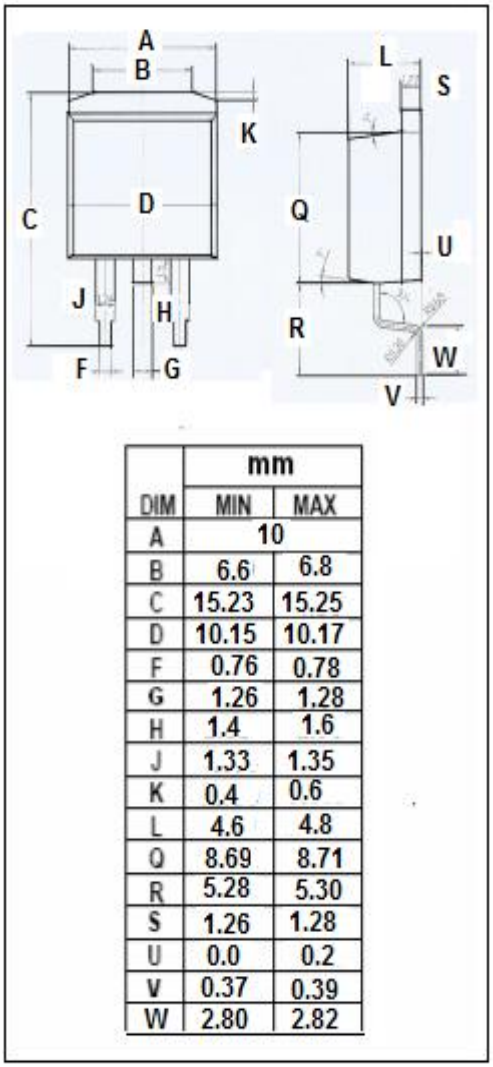
- **APPLICATIONS**
- Power supply
- Switching applications

- **ABSOLUTE MAXIMUM RATINGS(T_a=25℃)**

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	250	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-Continuous	64	A
P_D	Total Dissipation @T_C=25℃	300	W
T_j	Max. Operating Junction Temperature	-55~175	℃
T_{stg}	Storage Temperature	-55~175	℃

- **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
Rth(j-c)	Channel-to-case thermal resistance	0.5	℃/W



DIM	mm MIN	MAX
A	10	
B	6.6	6.8
C	15.23	15.25
D	10.15	10.17
F	0.76	0.78
G	1.26	1.28
H	1.4	1.6
J	1.33	1.35
K	0.4	0.6
L	4.6	4.8
Q	8.69	8.71
R	5.28	5.30
S	1.26	1.28
U	0.0	0.2
V	0.37	0.39
W	2.80	2.82

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D= 1mA	250			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}; I_D= 270uA	2	3	4	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D= 64A		17.5	20	mΩ
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±20V; V_{DS}= 0V		±1	±100	nA
I_{DSS}	Drain-Source Leakage Current	V_{DS}= 200V; V_{GS}= 0V		0.1	1	μA
V_{SD}	Diode forward voltage	I_S= 64A, V_{GS} = 0V		1	1.2	V